30 V, 2 A NPN low VCEsat (BISS) transistor

23 August 2013

Product data sheet

1. General description

NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

PNP complement: PBSS5230QA.

2. Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain h_{FE} at high I_C
- High energy efficiency due to less heat generation
- Reduced Printed-Circuit Board (PCB) area requirements
- Solderable side pads
- AEC-Q101 qualified

3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	30	V
I _C	collector current		-	-	2	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	3	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le 300 \text{ μs}; \delta \le 0.02 ; T_{amb}$ = 25 °C	-	135	180	mΩ



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		C
2	Е	emitter		В
3	С	collector	4 3	- 12
4	С	collector	2	E sym123
			Transparent top view DFN1010D-3 (SOT1215)	

6. Ordering information

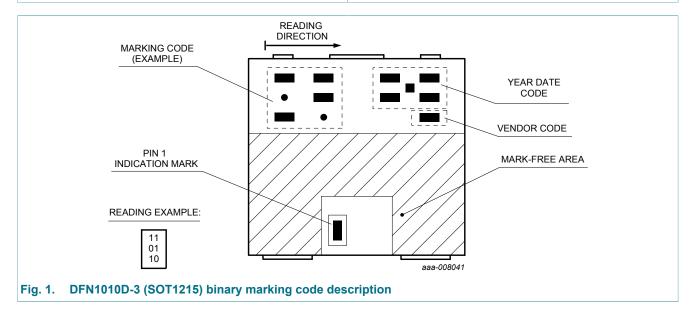
Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBSS4230QA	DFN1010D-3	plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals	SOT1215			

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS4230QA	01 11 00



PBSS4230QA

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Limiting values

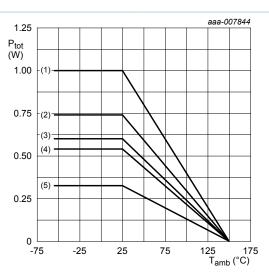
Table 5. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	30	V
V_{CEO}	collector-emitter voltage	open base		-	30	V
V_{EBO}	emitter-base voltage	open collector		-	7	V
I _C	collector current			-	2	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	3	Α
I _B	base current			-	0.3	Α
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	1	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	325	mW
			[2]	-	600	mW
			[3]	-	740	mW
			[4]	-	540	mW
			[5]	-	1000	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- Device mounted on an FR4 PCB single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².
- Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, 4-layer copper, tin-plated mounting pad for collector 1 cm².

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- (1) FR4 PCB, 4-layer copper, 1 cm²
- (2) FR4 PCB, single-sided copper, 6 cm²
- (3) FR4 PCB, single-sided copper, 1 cm²
- (4) FR4 PCB, 4-layer copper, standard footprint
- (5) FR4 PCB, single-sided copper, standard footprint

Fig. 2. Power derating curves

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	R _{th(j-a)} thermal resistance from junction to ambient	in free air	[1]	-	-	385	K/W
			<u>[2]</u>	-	-	209	K/W
all			[3]	-	-	169	K/W
			<u>[4]</u>	-	-	232	K/W
			[5]	-	-	125	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 1 cm².
- Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated mounting pad for collector 1 cm².

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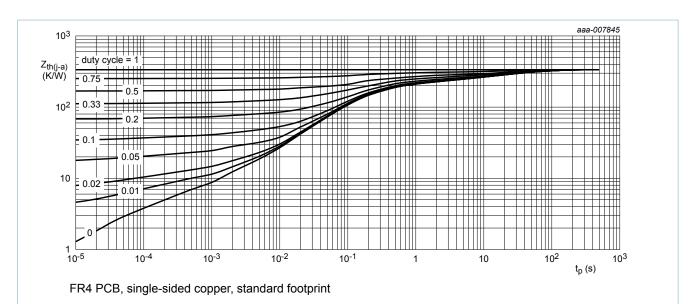


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

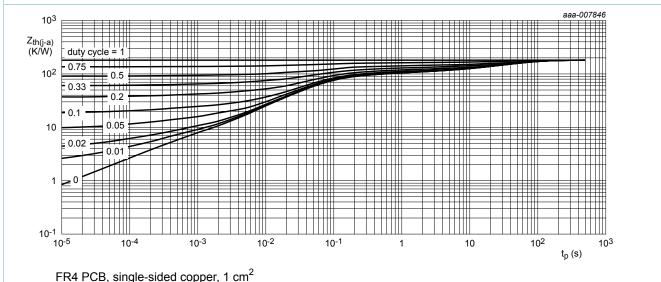


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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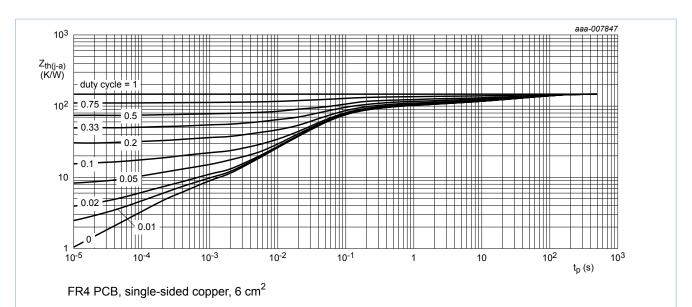


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

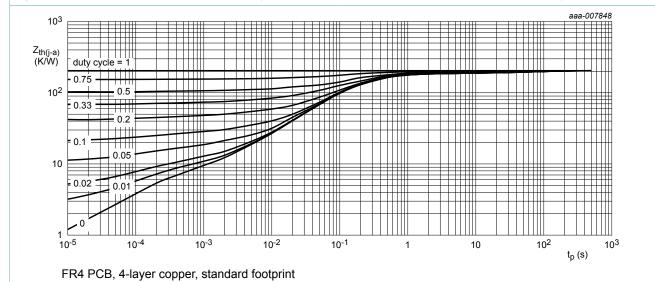
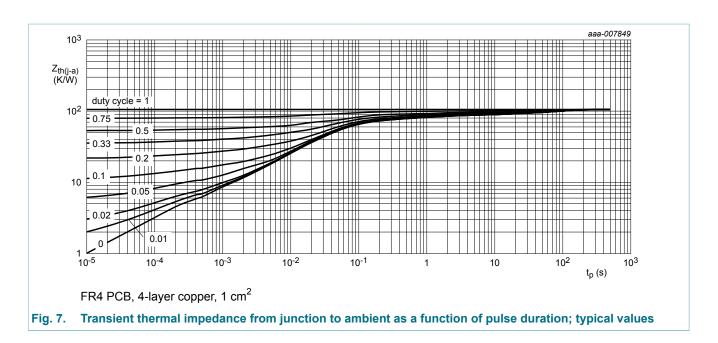


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

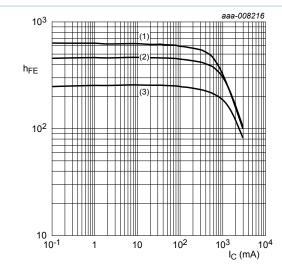
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 24 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 24 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = 24 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 2 V; I_{C} = 100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	250	430	-	
		V_{CE} = 2 V; I_{C} = 500 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	230	380	-	
		V_{CE} = 2 V; I_{C} = 1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	180	290	-	
		V_{CE} = 2 V; I_{C} = 2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	100	160	-	
V _{CEsat}	collector-emitter saturation voltage	I_{C} = 500 mA; I_{B} = 50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	75	100	mV
		I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le 300$ μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	140	190	mV
		I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	135	180	mV

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		I_{C} = 2 A; I_{B} = 100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	265	360	mV
		$I_C = 2 \text{ A}; I_B = 200 \text{ mA}; \text{ pulsed};$ $t_p \le 300 \text{ µs}; \delta \le 0.02 ; T_{amb} = 25 ^{\circ}\text{C}$	-	255	350	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le 300 \ \mu s$; δ ≤ 0.02 ; T_{amb} = 25 °C	-	135	180	mΩ
V _{BEsat} base-emitter saturation voltage	base-emitter saturation voltage	I_C = 500 mA; I_B = 50 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$; T_{amb} = 25 °C	-	0.86	1	V
		I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le 300 \ \mu s$; δ ≤ 0.02 ; T_{amb} = 25 °C	-	0.9	1.05	V
		I_C = 2 A; I_B = 100 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02 \ ; \ T_{amb}$ = 25 °C	-	1	1.15	V
		I_C = 2 A; I_B = 200 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02 \ ; \ T_{amb}$ = 25 °C	-	1.05	1.2	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I_{C} = 0.5 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	0.75	0.9	V
t _d	delay time	V _{CC} = 10 V; I _C = 0.5 A; I _{Bon} = 25 mA;	-	15	-	ns
t _r	rise time	I _{Boff} = -25 mA; T _{amb} = 25 °C	-	30	-	ns
t _{on}	turn-on time		-	45	-	ns
t _s	storage time	_	-	425	-	ns
t _f	fall time		-	65	-	ns
t _{off}	turn-off time		-	490	-	ns
f⊤	transition frequency	V_{CE} = 10 V; I_{C} = 50 mA; f = 100 MHz; T_{amb} = 25 °C	130	190	-	MHz
C _c	collector capacitance	V _{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	8	10	pF

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$$V_{CE} = 2 V$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 8. DC current gain as a function of collector current; typical values

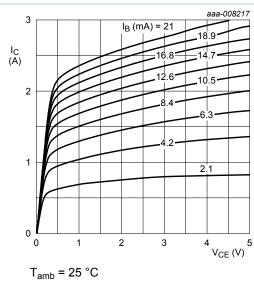
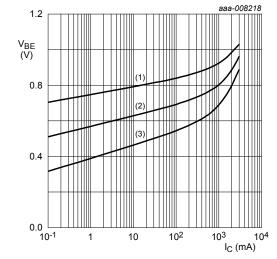


Fig. 9. Collector current as a function of collectoremitter voltage; typical values



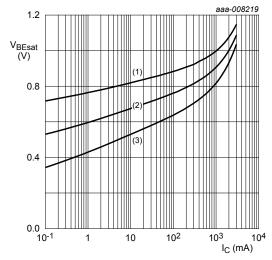
$$V_{CE} = 2 V$$

(1)
$$T_{amb} = -55 \,^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 10. Base-emitter voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

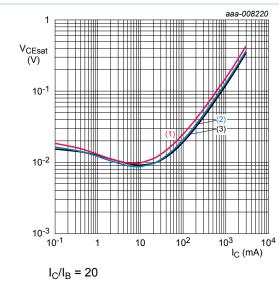
(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 11. Base-emitter saturation voltage as a function of collector current; typical values

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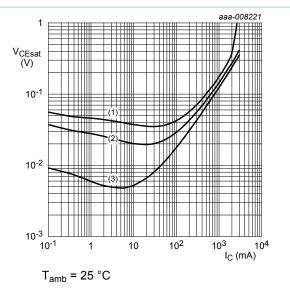


(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = -55 °C$$

Fig. 12. Collector-emitter saturation voltage as a function of collector current; typical values

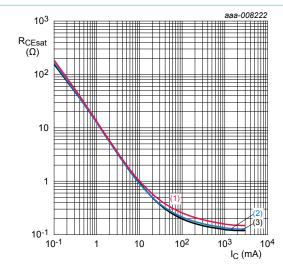


(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig. 13. Collector-emitter saturation voltage as a function of collector current; typical values



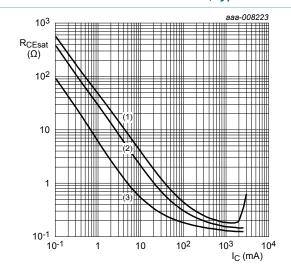
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 14. Collector-emitter saturation resistance as a function of collector current; typical values



$$T_{amb}$$
 = 25 °C

(1)
$$I_C/I_B = 100$$

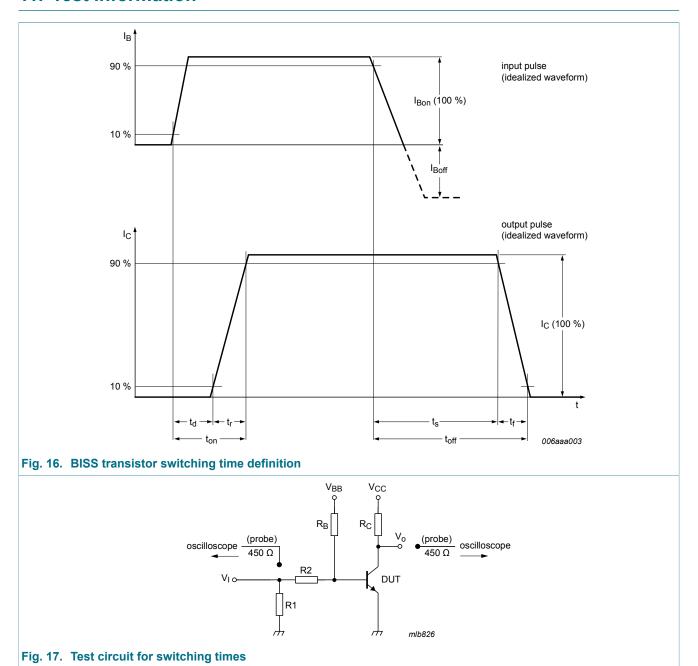
(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig. 15. Collector-emitter saturation resistance as a function of collector current; typical values

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11. Test information

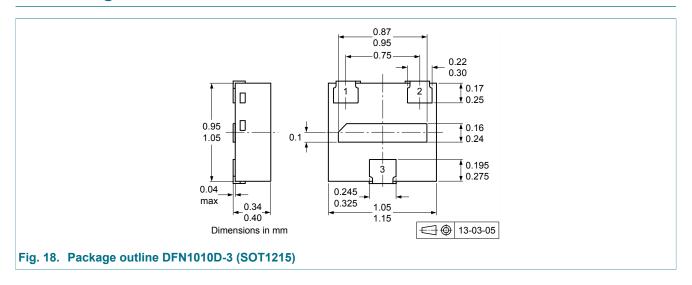


11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

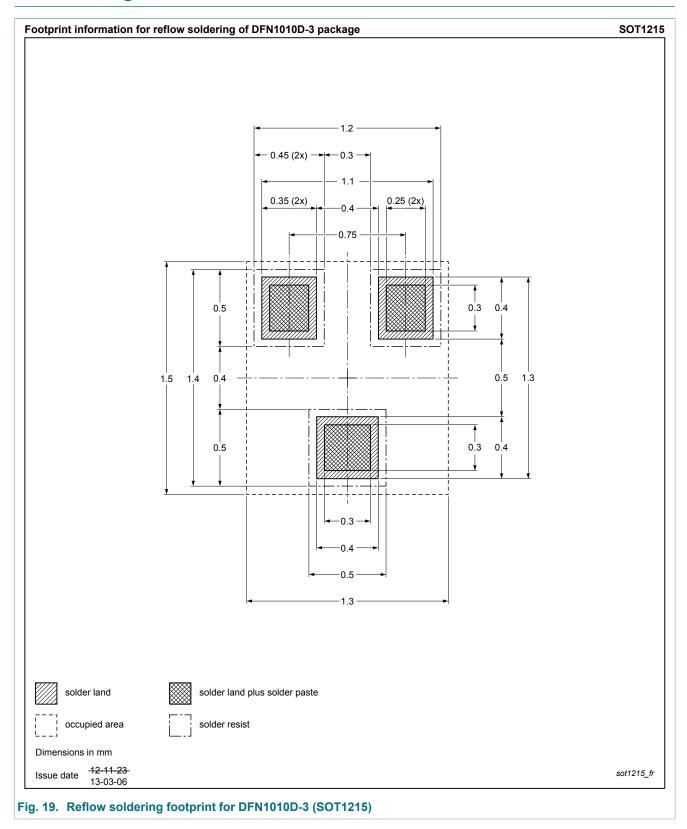
30 V, 2 A NPN low VCEsat (BISS) transistor

12. Package outline



30 V, 2 A NPN low VCEsat (BISS) transistor

13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4230QA v.1	20130823	Product data sheet	-	-

30 V, 2 A NPN low VCEsat (BISS) transistor

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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